FDLL3595

HIGH CONDUCTANCE LOW LEAKAGE DIODE

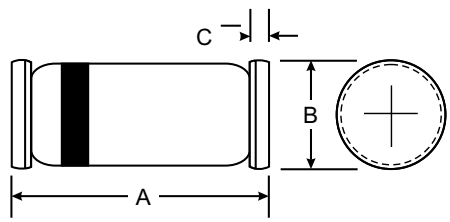
Features

- Fast Switching Speed
- General Purpose Rectification
- Silicon Epitaxial Planar Construction

Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)

RoHS COMPLIANT



LL34/ SOD-80		
Dim	**Min**	**Max**
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Sym	Parameter	Value	Units
T_{stg}	Storage Temperature	-65 to +200	^{O}C
T_J	Operating Junction Temperature	-65 to +200	^{O}C
P_D	Total Power Dissipation at T_A = 25^{O}C	500	mW
	Linear Derating Factor from T_A = 25^{O}C	3.33	mW/^{O}C
R_{OJA}	Thermal Resistance Junction-to-Ambient	350	^{O}C/W
W_{iv}	Working Inverse Voltage	125	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current (IF)	500	mA
i_f	Recurrent Peak Forward Current	600	mA
$i_{F(surge)}$	Peak Forward Surge Current (IFSM) Pulse Width = 1.0 second	1.0	Amp
	Pulse Width = 1.0 microsecond	4.0	Amp

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B_V	Breakdown Voltage	150		V	I_R = 100 uA
I_R	Reverse Leakage		1.0	nA	V_R = 125 V
			300	nA	V_R = 30 V T_A = 125^{O}C
			500	nA	V_R = 125 V T_A = 125^{O}C
			3.0	uA	V_R = 180 V T_A = 150^{O}C
V_F	Forward Voltage	520	680	mV	I_F = 1.0 mA
		600	750	mV	I_F = 5.0 mA
		650	800	mV	I_F = 10 mA
		750	880	mV	I_F = 50 mA
		790	920	mV	I_F = 100 mA
		0.83	1.00	V	I_F = 200 mA
C_T	Capacitance		8.0	pF	V_R = 0.0 V, f = 1.0 MHz
T_{RR}	Reverse Recovery Time		3.0	us	I_F = 10 mA V_R = 3.5 V R_L = 1.0 kOhms